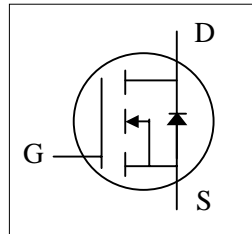




- Simple Drive Requirement**
- Low On-resistance**
- Fast Switching Characteristics**

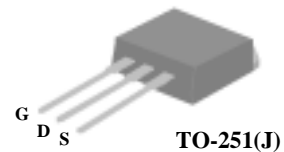
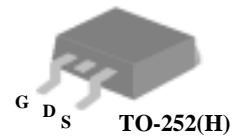


BV_{DSS}	900V
$R_{DS(ON)}$	7.2
I_D	1.9A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The through-hole version (AP02N90J) is available for low-profile applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	900	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C=25$	Continuous Drain Current, $V_{GS} @ 10V$	1.9	A
$I_D @ T_C=100$	Continuous Drain Current, $V_{GS} @ 10V$	1.2	A
I_{DM}	Pulsed Drain Current ¹	6	A
$P_D @ T_C=25$	Total Power Dissipation	62.5	W
	Linear Derating Factor	0.5	W/
E_{AS}	Single Pulse Avalanche Energy ²	36	mJ
I_{AR}	Avalanche Current	1.9	A
T_{STG}	Storage Temperature Range	-55 to 150	
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case	Max. 2.0	/W
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	/W



AP02N90H/J

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	900	-	-	V
BV_{DSS}/T_j	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1mA$	-	0.8	-	V/
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=0.85A$	-	-	7.2	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=1.9A$	-	2	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^{\circ}\text{C}$)	$V_{DS}=900V, V_{GS}=0V$	-	-	10	μA
	Drain-Source Leakage Current ($T_j=125^{\circ}\text{C}$)	$V_{DS}=720V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	± 100	nA
Q_g	Total Gate Charge ³	$I_D=1.9A$	-	12	20	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=540V$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	4.7	-	nC
$t_{d(on)}$	Turn-on Delay Time ³	$V_{DD}=450V$	-	10	-	ns
t_r	Rise Time	$I_D=1.9A$	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\ \Omega, V_{GS}=10V$	-	18	-	ns
t_f	Fall Time	$R_D=236\ \Omega$	-	9	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	630	1000	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	40	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	4	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ³	$I_S=1.9A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_S=1.9A, V_{GS}=0V,$	-	360	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	1.8	-	μC

Notes:

1. Pulse width limited by safe operating area.
2. Starting $T_j=25^{\circ}\text{C}$, $V_{DD}=50V$, $L=20mH$, $R_G=25\ \Omega$, $I_{AS}=1.9A$.
3. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

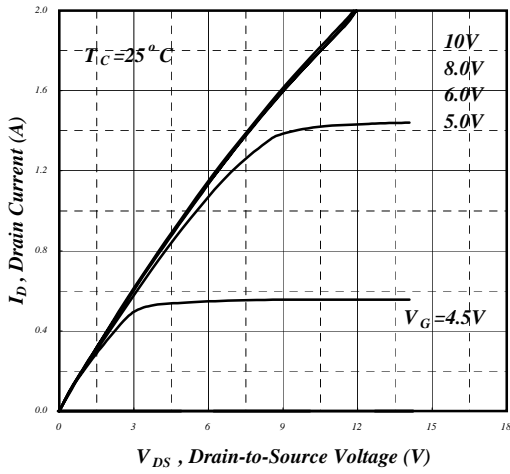


Fig 1. Typical Output Characteristics

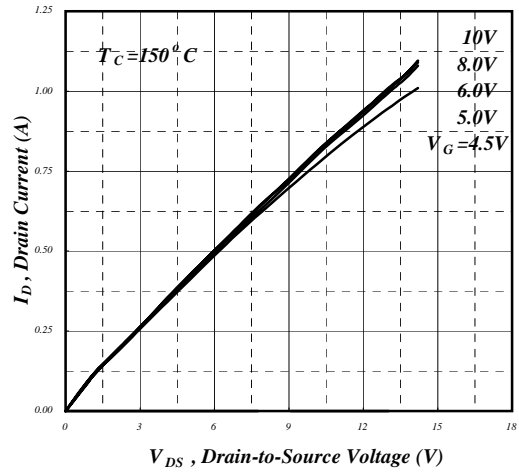


Fig 2. Typical Output Characteristics

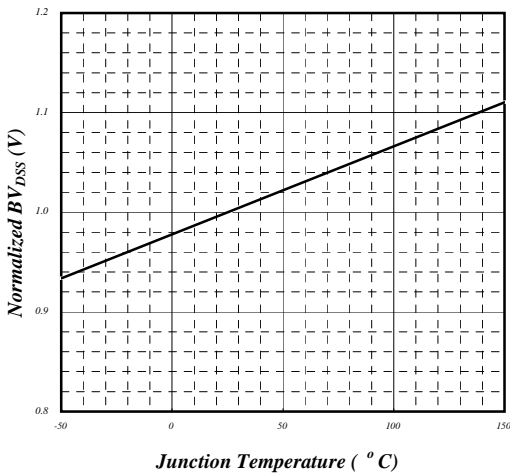


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

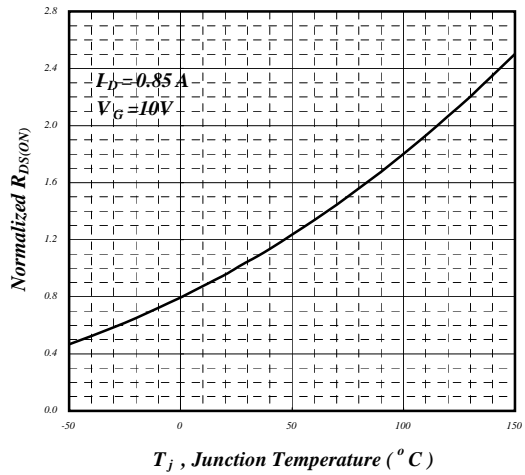


Fig 4. Normalized On-Resistance v.s. Junction Temperature

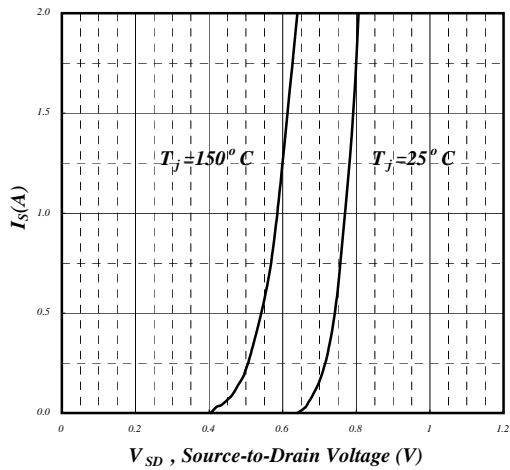


Fig 5. Forward Characteristic of Reverse Diode

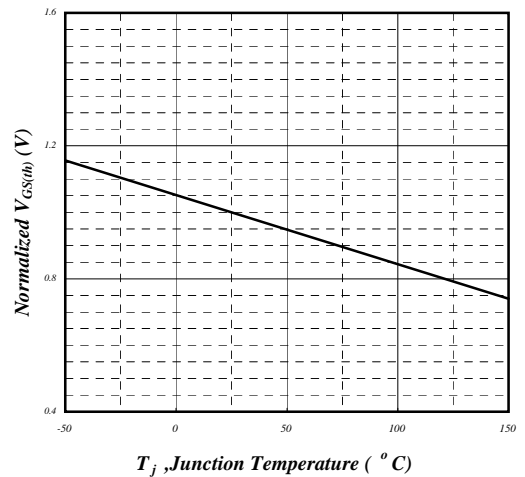


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

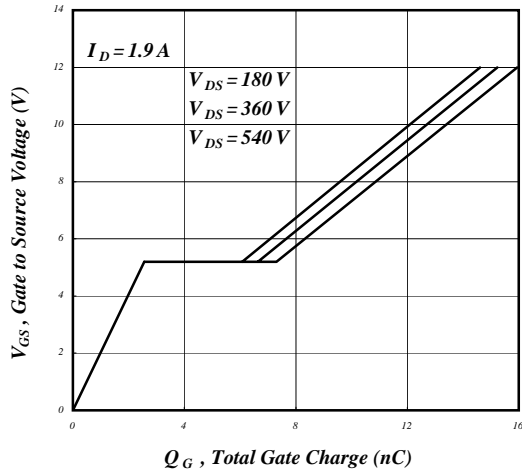


Fig 7. Gate Charge Characteristics

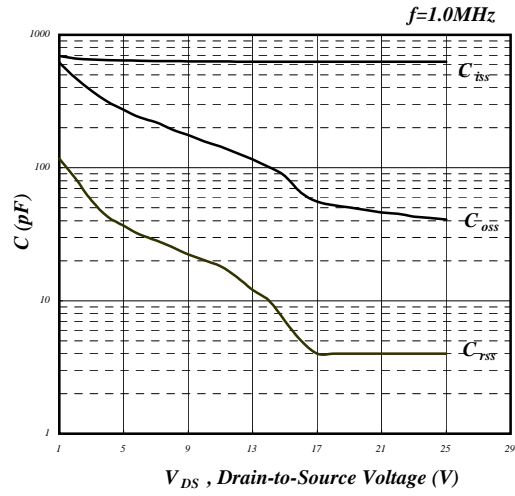


Fig 8. Typical Capacitance Characteristics

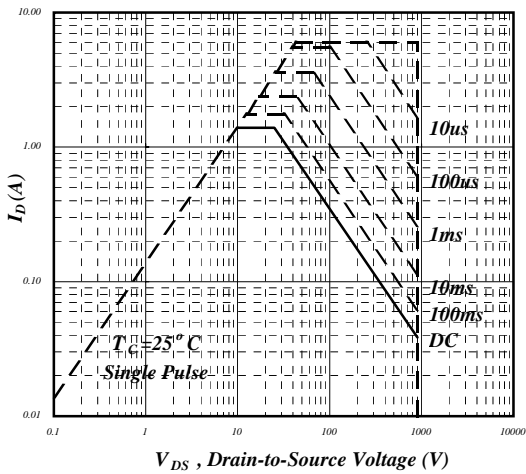


Fig 9. Maximum Safe Operating Area

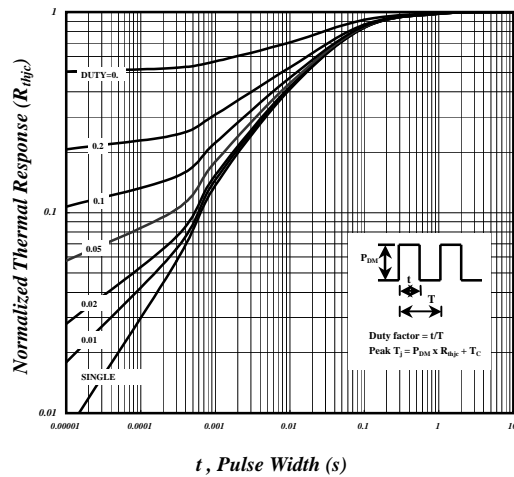


Fig 10. Effective Transient Thermal Impedance

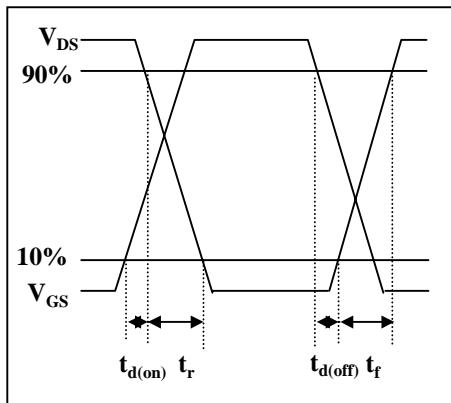


Fig 11. Switching Time Waveform

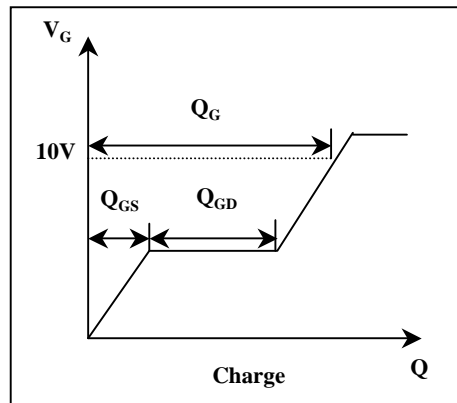


Fig 12. Gate Charge Waveform